7.4 **EEPROM Data Memory**

The Atmel[®] ATmega328P contains 1Kbyte of data EEPROM memory. It is organized as a separate data space, in which single bytes can be read and written. The EEPROM has an endurance of at least 100,000 write/erase cycles. The access between the EEPROM and the CPU is described in the following, specifying the EEPROM address registers, the EEPROM data register, and the EEPROM control register.

Section 27. "Memory Programming" on page 241 contains a detailed description on EEPROM programming in SPI or parallel programming mode.

7.4.1 **EEPROM Read/Write Access**

The EEPROM access registers are accessible in the I/O space.

The write access time for the EEPROM is given in Table 7-2 on page 22. A self-timing function, however, lets the user software detect when the next byte can be written. If the user code contains instructions that write the EEPROM, some precautions must be taken. In heavily filtered power supplies, V_{CC} is likely to rise or fall slowly on power-up/down. This causes the device for some period of time to run at a voltage lower than specified as minimum for the clock frequency used. See Section 7.4.2 "Preventing EEPROM Corruption" on page 19 for details on how to avoid problems in these situations.

In order to prevent unintentional EEPROM writes, a specific write procedure must be followed. Refer to the description of the EEPROM control register for details on this.

When the EEPROM is read, the CPU is halted for four clock cycles before the next instruction is executed. When the EEPROM is written, the CPU is halted for two clock cycles before the next instruction is executed.

7.4.2 **Preventing EEPROM Corruption**

During periods of low V_{CC.} the EEPROM data can be corrupted because the supply voltage is too low for the CPU and the EEPROM to operate properly. These issues are the same as for board level systems using EEPROM, and the same design solutions should be applied.

An EEPROM data corruption can be caused by two situations when the voltage is too low. First, a regular write sequence to the EEPROM requires a minimum voltage to operate correctly. Secondly, the CPU itself can execute instructions incorrectly, if the supply voltage is too low.

EEPROM data corruption can easily be avoided by following this design recommendation:

Keep the AVR RESET active (low) during periods of insufficient power supply voltage. This can be done by enabling the internal brown-out detector (BOD). If the detection level of the internal BOD does not match the needed detection level, an external low V_{CC} reset protection circuit can be used. If a reset occurs while a write operation is in progress, the write operation will be completed provided that the power supply voltage is sufficient.

7.5 I/O Memory

The I/O space definition of the ATmega328P is shown in Section "" on page 275.

All ATmega328P I/Os and peripherals are placed in the I/O space. All I/O locations may be accessed by the LD/LDS/LDD and ST/STS/STD instructions, transferring data between the 32 general purpose working registers and the I/O space, I/O registers within the address range 0x00 - 0x1F are directly bit-accessible using the SBI and CBI instructions. In these registers, the value of single bits can be checked by using the SBIS and SBIC instructions. Refer to the instruction set section for more details. When using the I/O specific commands IN and OUT, the I/O addresses 0x00 - 0x3F must be used. When addressing I/O registers as data space using LD and ST instructions, 0x20 must be added to these addresses. The ATmega328P is a complex microcontroller with more peripheral units than can be supported within the 64 location reserved in opcode for the IN and OUT instructions. For the extended I/O space from 0x60 - 0xFF in SRAM, only the ST/STS/STD and LD/LDS/LDD instructions can be used.

For compatibility with future devices, reserved bits should be written to zero if accessed. Reserved I/O memory addresses should never be written.

Some of the status flags are cleared by writing a logical one to them. Note that, unlike most other AVR®, the CBI and SBI instructions will only operate on the specified bit, and can therefore be used on registers containing such status flags. The CBI and SBI instructions work with registers 0x00 to 0x1F only.

The I/O and peripherals control registers are explained in later sections.



7.5.1 General Purpose I/O Registers

The Atmel[®] ATmega328P contains three general purpose I/O registers. These registers can be used for storing any information, and they are particularly useful for storing global variables and status flags. General purpose I/O registers within the address range 0x00 - 0x1F are directly bit-accessible using the SBI, CBI, SBIS, and SBIC instructions.

7.6 Register Description

7.6.1 EEARH and EEARL – The EEPROM Address Register

Bit	15	14	13	12	11	10	9	8	
0x22 (0x42)	-	_	-	-	-	-	-	EEAR8	EEARH
0x21 (0x41)	EEAR7	EEAR6	EEAR5	EEAR4	EEAR3	EEAR2	EEAR1	EEAR0	EEARL
	7	6	5	4	3	2	1	0	l
Read/Write	R	R	R	R	R	R	R	R/W	
	R/W								
Initial Value	0	0	0	0	0	0	0	X	
	Χ	Χ	Χ	Χ	Χ	Χ	Χ	X	

. Bits 15..9 - Res: Reserved Bits

These bits are reserved bits in the Atmel ATmega328P and will always read as zero.

• Bits 8..0 - EEAR8..0: EEPROM Address

The EEPROM address registers – EEARH and EEARL specify the EEPROM address in the 256/512/512/1K bytes EEPROM space. The EEPROM data bytes are addressed linearly between 0 and 255/511/511/1023. The initial value of EEAR is undefined. A proper value must be written before the EEPROM may be accessed.

EEAR8 is an unused bit in ATmega328P and must always be written to zero.

7.6.2 EEDR – The EEPROM Data Register

Bit	7	6	5	4	3	2	1	0	
0x20 (0x40)	MSB							LSB	EEDR
Read/Write	R/W	•							
Initial Value	0	0	0	0	0	0	0	0	

• Bits 7..0 - EEDR7.0: EEPROM Data

For the EEPROM write operation, the EEDR register contains the data to be written to the EEPROM in the address given by the EEAR register. For the EEPROM read operation, the EEDR contains the data read out from the EEPROM at the address given by EEAR.

7.6.3 EECR – The EEPROM Control Register

Bit	7	6	5	4	3	2	1	0	
0x1F (0x3F)	-	-	EEPM1	EEPM0	EERIE	EEMPE	EEPE	EERE	EECR
Read/Write	R	R	R/W	R/W	R/W	R/W	R/W	R/W	
Initial Value	0	0	X	X	0	0	Χ	0	

• Bits 7..6 - Res: Reserved Bits

These bits are reserved bits in the Atmel ATmega328P and will always read as zero.

• Bits 5, 4 – EEPM1 and EEPM0: EEPROM Programming Mode Bits

The EEPROM programming mode bit setting defines which programming action that will be triggered when writing EEPE. It is possible to program data in one atomic operation (erase the old value and program the new value) or to split the erase and write operations in two different operations. The programming times for the different modes are shown in Table 7-1. While EEPE is set, any write to EEPMn will be ignored. During reset, the EEPMn bits will be reset to 0b00 unless the EEPROM is busy programming.



Table 7-1. EEPROM Mode Bits

EEPM1	EEPM0	Programming Time	Operation
0	0	3.4ms	Erase and write in one operation (atomic operation)
0	1	1.8ms	Erase only
1	0	1.8ms	Write only
1	1	_	Reserved for future use

• Bit 3 - EERIE: EEPROM Ready Interrupt Enable

Writing EERIE to one enables the EEPROM ready interrupt if the I bit in SREG is set. Writing EERIE to zero disables the interrupt. The EEPROM ready interrupt generates a constant interrupt when EEPE is cleared. The interrupt will not be generated during EEPROM write or SPM.

• Bit 2 - EEMPE: EEPROM Master Write Enable

The EEMPE bit determines whether setting EEPE to one causes the EEPROM to be written. When EEMPE is set, setting EEPE within four clock cycles will write data to the EEPROM at the selected address If EEMPE is zero, setting EEPE will have no effect. When EEMPE has been written to one by software, hardware clears the bit to zero after four clock cycles. See the description of the EEPE bit for an EEPROM write procedure.

• Bit 1 - EEPE: EEPROM Write Enable

The EEPROM Write enable signal EEPE is the write strobe to the EEPROM. When address and data are correctly set up, the EEPE bit must be written to one to write the value into the EEPROM. The EEMPE bit must be written to one before a logical one is written to EEPE, otherwise no EEPROM write takes place. The following procedure should be followed when writing the EEPROM (the order of steps 3 and 4 is not essential):

- Wait until EEPE becomes zero.
- 2. Wait until SELFPRGEN in SPMCSR becomes zero.
- 3. Write new EEPROM address to EEAR (optional).
- Write new EEPROM data to EEDR (optional).
- 5. Write a logical one to the EEMPE bit while writing a zero to EEPE in EECR.
- 6. Within four clock cycles after setting EEMPE, write a logical one to EEPE.

The EEPROM can not be programmed during a CPU write to the flash memory. The software must check that the flash programming is completed before initiating a new EEPROM write. Step 2 is only relevant if the software contains a boot loader allowing the CPU to program the flash. If the flash is never being updated by the CPU, step 2 can be omitted. See Section 26. "Boot Loader Support – Read-While-Write Self-Programming" on page 229 for details about boot programming.

Caution:

An interrupt between step 5 and step 6 will make the write cycle fail, since the EEPROM master write enable will time-out. If an interrupt routine accessing the EEPROM is interrupting another EEPROM access, the EEAR or EEDR register will be modified, causing the interrupted EEPROM access to fail. It is recommended to have the global interrupt flag cleared during all the steps to avoid these problems.

When the write access time has elapsed, the EEPE bit is cleared by hardware. The user software can poll this bit and wait for a zero before writing the next byte. When EEPE has been set, the CPU is halted for two cycles before the next instruction is executed.

• Bit 0 - EERE: EEPROM Read Enable

The EEPROM read enable signal EERE is the read strobe to the EEPROM. When the correct address is set up in the EEAR register, the EERE bit must be written to a logic one to trigger the EEPROM read. The EEPROM read access takes one instruction, and the requested data is available immediately. When the EEPROM is read, the CPU is halted for four cycles before the next instruction is executed.

The user should poll the EEPE bit before starting the read operation. If a write operation is in progress, it is neither possible to read the EEPROM, nor to change the EEAR register.



The calibrated oscillator is used to time the EEPROM accesses. Table 7-2 lists the typical programming time for EEPROM access from the CPU.

Table 7-2. EEPROM Programming Time

Symbol	Number of Calibrated RC Oscillator Cycles	Typical Programming Time
EEPROM write (from CPU)	26,368	3.3ms

The following code examples show one assembly and one C function for writing to the EEPROM. The examples assume that interrupts are controlled (e.g. by disabling interrupts globally) so that no interrupts will occur during execution of these functions. The examples also assume that no flash boot loader is present in the software. If such code is present, the EEPROM write function must also wait for any ongoing SPM command to finish.

```
Assembly Code Example
       EEPROM_write:
              ; Wait for completion of previous write
              sbic     EECR,EEPE
rjmp     EEPROM_write
              ; Set up address (r18:r17) in address register
              out EEARH, r18
              out
                    EEARL, r17
              ; Write data (r16) to Data Register
                    EEDR,r16
              ; Write logical one to EEMPE
                    EECR, EEMPE
              ; Start eeprom write by setting EEPE
                    EECR, EEPE
              sbi
              ret
C Code Example
       void EEPROM_write(unsigned int uiAddress, unsigned char ucData)
              /* Wait for completion of previous write */
              while(EECR & (1<<EEPE))</pre>
              /* Set up address and Data Registers */
              EEAR = uiAddress;
              EEDR = ucData;
              /* Write logical one to EEMPE */
              EECR \mid = (1 < < EEMPE);
              /* Start eeprom write by setting EEPE */
              EECR = (1 < < EEPE);
```

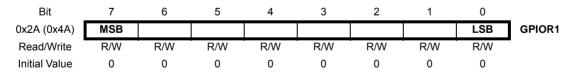
The next code examples show assembly and C functions for reading the EEPROM. The examples assume that interrupts are controlled so that no interrupts will occur during execution of these functions.

```
Assembly Code Example
       EEPROM_read:
              ; Wait for completion of previous write
              sbic
                      EECR, EEPE
              rimp
                      EEPROM read
              ; Set up address (r18:r17) in address register
                      EEARH, r18
              out
                      EEARL, r17
              out
              ; Start eeprom read by writing EERE
                      EECR, EERE
              ; Read data from Data Register
                      r16,EEDR
              in
              ret
C Code Example
       unsigned char EEPROM_read(unsigned int uiAddress)
              /* Wait for completion of previous write */
              while(EECR & (1<<EEPE))</pre>
              /* Set up address register */
              EEAR = uiAddress;
              /* Start eeprom read by writing EERE */
              EECR \mid = (1 < < EERE);
              /* Return data from Data Register */
              return EEDR;
```

7.6.4 GPIOR2 - General Purpose I/O Register 2

Bit	7	6	5	4	3	2	1	0	
0x2B (0x4B)	MSB							LSB	GPIOR2
Read/Write	R/W								
Initial Value	0	0	0	0	0	0	0	0	

GPIOR1 - General Purpose I/O Register 1 7.6.5



GPIOR0 - General Purpose I/O Register 0

Bit	7	6	5	4	3	2	1	0	
0x1E (0x3E)	MSB							LSB	GPIOR0
Read/Write	R/W	-							
Initial Value	0	0	0	0	0	0	0	0	

